












Author Correction: High carrier mobility in graphene doped using a monolayer of tungsten oxyselenide

Min Sup Choi, Ankur Nipane, Brian S. Y. Kim, Mark E. Ziffer, Ipshita Datta, Abhinandan Borah, Younghun Jung, Bumho Kim, Daniel Rhodes, Apoorv Jindal, Zachary A. Lamport, Myeongjin Lee, Amirali Zangiabadi , Maya N. Nair , Takashi Taniguchi , Kenji Watanabe , Ioannis Kymissis, Abhay N. Pasupathy , Michal Lipson , Xiaoyang Zhu, Won Jong Yoo , James Hone  and James T. Teherani 

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In the version of this article initially published, the first grant listed in the following was missing the final digit: “This work was primarily supported by the NSF MRSEC Program at Columbia in the Center for Precision-Assembled Quantum Materials (DMR-2011736 and DMR-1420634).” The error has been corrected in the online version of the article.

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